

# Fernando A. Ponce

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

330  
papers

11,746  
citations

52  
h-index

98  
g-index

357  
ext. papers

12,383  
ext. citations

3.2  
avg, IF

5.89  
L-index

#	Paper	IF	Citations
330	Realizing crack-free high-aluminum-mole-fraction AlGaIn on patterned GaN beyond the critical layer thickness. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 073103	2.5	0
329	Characterization of MOCVD regrown p-GaN and the interface properties for vertical GaN power devices. <i>Semiconductor Science and Technology</i> , <b>2021</b> , 36, 014005	1.8	1
328	The impact of interfacial Si contamination on GaN-on-GaN regrowth for high power vertical devices. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 222104	3.4	9
327	Selective area regrowth and doping for vertical gallium nitride power devices: Materials challenges and recent progress. <i>Materials Today</i> , <b>2021</b> , 49, 296-296	21.8	6
326	Nanostructured materials for high efficiency solar cells <b>2021</b> , 201-227		
325	Influence of substrate misorientation on the optical properties of Mg-doped GaN. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 195701	2.5	2
324	Investigation of polycrystalline Ga <sub>x</sub> In <sub>1-x</sub> for potential use as a solar cell absorber with tunable bandgap. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 073102	2.5	2
323	High Voltage Vertical GaN p-n Diodes With Hydrogen-Plasma Based Guard Rings. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 41, 127-130	4.4	33
322	Demonstration of GaN-based metal-insulator-semiconductor junction by hydrogen plasma treatment. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 052105	3.4	5
321	GaN Vertical-Channel Junction Field-Effect Transistors With Regrown p-GaN by MOCVD. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 3972-3977	2.9	12
320	The effect of low-angle off-axis GaN substrate orientation on the surface morphology of Mg-doped GaN epilayers. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 055301	2.5	1
319	Lateral and vertical growth of Mg-doped GaN on trench-patterned GaN films. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 102110	3.4	6
318	Identification of point defects using high-resolution electron energy loss spectroscopy. <i>Physical Review B</i> , <b>2019</b> , 99,	3.3	4
317	Non-uniform Mg distribution in GaN epilayers grown on mesa structures for applications in GaN power electronics. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 082102	3.4	17
316	Novel semiconductors for sustainable solar energy technologies. <i>Journal of Physics: Conference Series</i> , <b>2019</b> , 1173, 012001	0.3	2
315	Implantation-and etching-free high voltage vertical GaN p-n diodes terminated by plasma-hydrogenated p-GaN: revealing the role of thermal annealing. <i>Applied Physics Express</i> , <b>2019</b> , 12, 051015	2.4	20
314	Corrections to Lateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlattices [Aug 18 Art. no. 2400507]. <i>IEEE Journal of Quantum Electronics</i> , <b>2019</b> , 55, 1-1	2	1

313	Dopant profiling in p-i-n GaN structures using secondary electrons. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 015704	2.5	12
312	Evaluating the performance of InGaN/GaN multi-quantum-well solar cells operated at elevated temperatures via DC and small-signal AC analysis. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, 101003	1.4	
311	Effect of InAs quantum dots capped with GaAs on atomic-scale ordering in Ga <sub>0.5</sub> In <sub>0.5</sub> P. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 053104	2.5	0
310	Determination of electronic band structure by electron holography of etched-and-regrown interfaces in GaN p-i-n diodes. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 201602	3.4	11
309	Investigation of GaN-on-GaN vertical p-n diode with regrown p-GaN by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 233502	3.4	41
308	Nonpolar vertical GaN-on-GaN p <i>n</i> diodes grown on free-standing $\sqrt{10}$ m-plane GaN substrates. <i>Applied Physics Express</i> , <b>2018</b> , 11, 111003	2.4	10
307	Theory and Design of Electron Blocking Layers for III-N-Based Laser Diodes by Numerical Simulation. <i>IEEE Journal of Quantum Electronics</i> , <b>2018</b> , 54, 1-11	2	7
306	High Resolution EELS of Point Defects in a Nitride Semiconductor Material. <i>Microscopy and Microanalysis</i> , <b>2018</b> , 24, 430-431	0.5	
305	Dislocation baskets in thick In <sub>x</sub> Ga <sub>1-x</sub> N epilayers. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 105701	2.5	2
304	CdCl <sub>2</sub> passivation of polycrystalline CdMgTe and CdZnTe absorbers for tandem photovoltaic cells. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 203101	2.5	11
303	Lateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlattices. <i>IEEE Journal of Quantum Electronics</i> , <b>2018</b> , 54, 1-7	2	13
302	100-nm thick single-phase wurtzite BAlN films with boron contents over 10%. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254, 1600699	1.3	30
301	Sub 250 nm deep-UV AlGaN/AlN distributed Bragg reflectors. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 011105	3.4	23
300	Origin of high hole concentrations in Mg-doped GaN films. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254, 1600668	1.3	14
299	Plasticity and optical properties of GaN under highly localized nanoindentation stress fields. <i>Journal of Applied Physics</i> , <b>2017</b> , 121, 125105	2.5	19
298	Correlation between size distribution and luminescence properties of spool-shaped InAs quantum dots. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 055013	1.8	4
297	Refractory In <sub>x</sub> Ga <sub>1-x</sub> N Solar Cells for High-Temperature Applications. <i>IEEE Journal of Photovoltaics</i> , <b>2017</b> , 7, 1646-1652	3.7	21
296	Crystal structure and composition of BAlN thin films: Effect of boron concentration in the gas flow. <i>Journal of Crystal Growth</i> , <b>2017</b> , 475, 334-340	1.6	15

295	Stability of alloyed and nonalloyed ohmic contacts to n-type GaN at high temperature in air. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 126502	1.4	1
294	A review of the synthesis of reduced defect density In <sub>x</sub> Ga <sub>1-x</sub> N for all indium compositions. <i>Solid-State Electronics</i> , <b>2017</b> , 136, 3-11	1.7	14
293	High Reflectivity Hybrid AlGa <sub>N</sub> /Silver Distributed Bragg Reflectors for Use in the UV-Visible Spectrum. <i>IEEE Journal of Quantum Electronics</i> , <b>2017</b> , 53, 1-8	2	5
292	Temperature Dependence and High-Temperature Stability of the Annealed Ni/Au Ohmic Contact to p-Type GaN in Air. <i>Journal of Electronic Materials</i> , <b>2016</b> , 45, 2087-2091	1.9	8
291	Electrically conducting n-type AlGa <sub>N</sub> /Ga <sub>N</sub> distributed Bragg reflectors grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2016</b> , 443, 81-84	1.6	13
290	Development for ultraviolet vertical cavity surface emitting lasers <b>2016</b> ,		3
289	Early nucleation stages of low density InAs quantum dots nucleation on GaAs by MOVPE. <i>Journal of Crystal Growth</i> , <b>2016</b> , 434, 47-54	1.6	6
288	A new exposure model to evaluate smoked illicit drugs in rodents: A study of crack cocaine. <i>Journal of Pharmacological and Toxicological Methods</i> , <b>2016</b> , 77, 17-23	1.7	6
287	Local Strain Relaxation by A-type Dislocation Clusters in In <sub>x</sub> Ga <sub>1-x</sub> N/Ga <sub>N</sub> Film with Indium Compositions of x = 0.07 and 0.12. <i>Microscopy and Microanalysis</i> , <b>2016</b> , 22, 1572-1573	0.5	
286	Critical thickness investigation of MBE-grown GaInAs/GaAs and GaAsSb/GaAs heterostructures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2016</b> , 34, 02L113	1.3	8
285	Improved optical properties of InAs quantum dots for intermediate band solar cells by suppression of misfit strain relaxation. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 034301	2.5	12
284	Development of a high-band gap high temperature III-nitride solar cell for integration with concentrated solar power technology <b>2016</b> ,		3
283	Strain management of AlGa <sub>N</sub> -based distributed Bragg reflectors with Ga <sub>N</sub> interlayer grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 081103	3.4	12
282	Optically pumped vertical-cavity surface-emitting laser at 374.9 nm with an electrically conducting n-type distributed Bragg reflector. <i>Applied Physics Express</i> , <b>2016</b> , 9, 111002	2.4	14
281	Inverse-Tapered p-Waveguide for Vertical Hole Transport in High-[Al] AlGa <sub>N</sub> Emitters. <i>IEEE Photonics Technology Letters</i> , <b>2015</b> , 27, 1768-1771	2.2	8
280	Comprehensive study of the electronic and optical behavior of highly degenerate p-type Mg-doped Ga <sub>N</sub> and AlGa <sub>N</sub> . <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 045710	2.5	41
279	Effect of Group-III precursors on unintentional gallium incorporation during epitaxial growth of InAlN layers by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 125303	2.5	5
278	Onset of surface stimulated emission at 260 nm from AlGa <sub>N</sub> multiple quantum wells. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 241109	3.4	15

277	Growth of high-quality AlN layers on sapphire substrates at relatively low temperatures by metalorganic chemical vapor deposition. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 1089-1095	1.3	42
276	Strain Relaxation in InAs Quantum Dots and its Suppression by Indium Flushing. <i>Microscopy and Microanalysis</i> , <b>2015</b> , 21, 983-984	0.5	
275	Structural and Optical Properties of AlGaIn MQWs Grown by MOCVD Using One and Two TMG Sources. <i>Microscopy and Microanalysis</i> , <b>2015</b> , 21, 1681-1682	0.5	
274	High Spatial/Energy Resolution Band Gap Measurements: Delocalization and Other Effects in a Monochromated Cold FEG Nion Dedicated STEM. <i>Microscopy and Microanalysis</i> , <b>2015</b> , 21, 657-658	0.5	1
273	Temperature dependence of the crystalline quality of AlN layer grown on sapphire substrates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2015</b> , 414, 76-80	1.6	36
272	Low-temperature growth of InGaIn films over the entire composition range by MBE. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 115-118	1.6	30
271	Demonstration of transverse-magnetic deep-ultraviolet stimulated emission from AlGaIn multiple-quantum-well lasers grown on a sapphire substrate. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 041115	3.4	45
270	Optically pumped AlGaIn quantum-well lasers at sub-250 nm grown by MOCVD on AlN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 258-260		11
269	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. <i>Journal of Crystal Growth</i> , <b>2014</b> , 388, 143-149	1.6	40
268	InAs quantum dot growth on Al <sub>x</sub> Ga <sub>1-x</sub> As by metalorganic vapor phase epitaxy for intermediate band solar cells. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 093511	2.5	13
267	Compositional variations in In <sub>0.5</sub> Ga <sub>0.5</sub> N nanorods grown by molecular beam epitaxy. <i>Nanotechnology</i> , <b>2014</b> , 25, 215705	3.4	8
266	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. <i>Journal of Crystal Growth</i> , <b>2014</b> , 388, 137-142	1.6	43
265	Low-threshold stimulated emission at 249 nm and 256 nm from AlGaIn-based multiple-quantum-well lasers grown on sapphire substrates. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 141106	3.4	68
264	Simulations, Practical Limitations, and Novel Growth Technology for InGaIn-Based Solar Cells. <i>IEEE Journal of Photovoltaics</i> , <b>2014</b> , 4, 601-606	3.7	23
263	Optically pumped deep-ultraviolet AlGaIn multi-quantum-well lasers grown by metalorganic chemical vapor deposition <b>2014</b> ,		1
262	High Energy and Spatial Resolution EELS Band Gap Measurements Using a Nion Monochromated Cold Field Emission HERMES Dedicated STEM. <i>Microscopy and Microanalysis</i> , <b>2014</b> , 20, 70-71	0.5	2
261	Deep-ultraviolet lasing at 243 nm from photo-pumped AlGaIn/AlN heterostructure on AlN substrate. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 101110	3.4	66
260	Sub-250 nm low-threshold deep-ultraviolet AlGaIn-based heterostructure laser employing HfO <sub>2</sub> /SiO <sub>2</sub> dielectric mirrors. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 211103	3.4	30

259	Highly luminescent, high-indium-content InGaN film with uniform composition and full misfit-strain relaxation. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 131101	3.4	31
258	Improved Hole Transport by $\text{p-In}_x\text{Ga}_{1-x}\text{N}$ Layer in Multiple Quantum Wells of Visible LEDs. <i>IEEE Photonics Technology Letters</i> , <b>2013</b> , 25, 1789-1792	2.2	2
257	The effect of InGaN underlayers on the electronic and optical properties of InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 041115	3.4	17
256	The growth of In <sub>0.5</sub> Ga <sub>0.5</sub> N and InN layers on (1 1 1)Si using nanorod intermediate arrays. <i>Journal of Crystal Growth</i> , <b>2013</b> , 384, 55-60	1.6	2
255	Indium Nitride and Indium Gallium Nitride layers grown on nanorods. <i>Journal of Physics: Conference Series</i> , <b>2013</b> , 471, 012025	0.3	1
254	Capacitance Voltage Characteristics and Electron Holography on Cubic AlGaN/GaN Heterojunctions. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JN04	1.4	6
253	The effect of nanoscratching direction on the plastic deformation and surface morphology of InP crystals. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 203503	2.5	5
252	Hydrogen-related, deeply bound excitons in Mg-doped GaN films. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 082103	3.4	11
251	Strain-related optical properties of ZnO crystals due to nanoindentation on various surface orientations. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 183511	2.5	11
250	Stimulated emission at 257 nm from optically-pumped AlGaN/AlN heterostructure on AlN substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 1768-1770	1.6	5
249	Free carrier accumulation at cubic AlGaN/GaN heterojunctions. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 142108	3.4	9
248	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 161110	3.4	74
247	Compositional instability in InAlN/GaN lattice-matched epitaxy. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 092103	3.4	28
246	Early stages of mechanical deformation in indium phosphide with the zinc blende structure. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 063514	2.5	7
245	Correlated Structural, Electronic, and Optical Properties of AlN/GaN Multiple Quantum Disks in GaN Nanowires. <i>Applied Physics Express</i> , <b>2012</b> , 5, 025001	2.4	6
244	Microstructure and polarization fields in nitride semiconductors. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012001	0.3	1
243	Microstructure of nanoscratched semiconductors. <i>Journal of Physics: Conference Series</i> , <b>2011</b> , 326, 012061	0.3	13
242	Plastic hardening in cubic semiconductors by nanoscratching. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 013502	3.4	5

241	Transmission electron microscopy study of GaInNAs(Sb) thin films grown by atomic hydrogen-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 191907	3.4	13
240	Ammonothermal growth of high-quality GaN crystals on HVPE template seeds. <i>Journal of Crystal Growth</i> , <b>2011</b> , 318, 1030-1033	1.6	14
239	Electrostatic energy profiles at nanometer-scale in group III nitride semiconductors using electron holography. <i>Annalen Der Physik</i> , <b>2011</b> , 523, 75-86	2.6	11
238	Performance characteristics of InAlGaN laser diodes depending on electron blocking layer and waveguiding layer design grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2011</b> , 315, 272-277	1.6	5
237	Optimization of growth conditions for InGaAs/InAlAs/InP quantum cascade lasers by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2011</b> , 316, 75-80	1.6	17
236	High quality a-plane GaN films grown on cone-shaped patterned r-plane sapphire substrates. <i>Thin Solid Films</i> , <b>2011</b> , 519, 2508-2512	2.2	7
235	Reduction of structural defects in a-plane GaN epitaxy by use of periodic hemispherical patterns in r-plane sapphire substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2011</b> , 29, 021005	1.3	2
234	Effect of misfit dislocations on luminescence in m-plane InGaN quantum wells. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 261914	3.4	14
233	Effect of Growth Temperature on the Electron-Blocking Performance of InAlN Layers in Green Emitting Diodes. <i>Applied Physics Express</i> , <b>2010</b> , 3, 031003	2.4	4
232	Strain Relaxation Mechanisms in AlGaIn Epitaxy on AlN Templates. <i>Applied Physics Express</i> , <b>2010</b> , 3, 111003	3.4	18
231	Growth of linearly ordered arrays of InAs nanocrystals on scratched InP. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 054313	2.5	5
230	Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 221105	3.4	168
229	Carrier localization and nonradiative recombination in yellow emitting InGaIn quantum wells. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 031906	3.4	44
228	Improvement of quantum efficiency by employing active-layer-friendly lattice-matched InAlN electron blocking layer in green light-emitting diodes. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 101102	3.4	80
227	Misfit strain relaxation in m-plane epitaxy of InGaIn on ZnO. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 071909	3.4	5
226	Performance improvement of InGaIn-based laser diodes by epitaxial layer structure design <b>2010</b> ,		2
225	In-plane polarization of GaN-based heterostructures with arbitrary crystal orientation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 2226-2232	1.6	17
224	Polarization effects in 2-DEG and 2-DHG AlGaIn/AlN/GaN multi-heterostructures measured by electron holography. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1722-1724	1.3	6

223	Preface: Phys. Status Solidi C 7/1. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 7-8		4
222	Donor-related cathodoluminescence of p-AlGaIn electron blocking layer embedded in ultraviolet laser diode structure. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 211103	3.4	1
221	Misfit Strain Relaxation by Stacking Fault Generation in InGaIn Quantum Wells Grown on m-Plane GaN. <i>Applied Physics Express</i> , <b>2009</b> , 2, 041002	2.4	60
220	Evidence of Two-Dimensional Hole Gas in p-Type AlGaIn/AlN/GaN Heterostructures. <i>Applied Physics Express</i> , <b>2009</b> , 2, 121001	2.4	12
219	Comparative Study on MOCVD Growth of a-Plane GaIn Films on r-Plane Sapphire Substrates Using GaIn, AlGaIn, and AlN Buffer Layers. <i>Journal of Electronic Materials</i> , <b>2009</b> , 38, 1938-1943	1.9	20
218	Preface: Phys. Status Solidi A 206/2. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2009</b> , 206, 193-194	1.6	
217	Measurement of the solubility of ammonia and nitrogen in gallium at atmospheric pressure. <i>Journal of Alloys and Compounds</i> , <b>2009</b> , 467, 611-613	5.7	5
216	Highly conductive modulation doped composition graded p-AlGaIn/(AlN)/GaIn multiheterostructures grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 013720	2.5	13
215	Control of quantum-confined Stark effect in InGaIn/GaN multiple quantum well active region by p-type layer for III-nitride-based visible light emitting diodes. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 101113	3.4	53
214	Blue light emitting diodes grown on freestanding (11-20) a-plane GaIn substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 011123	3.4	23
213	Atomic Arrangement at the AlN/Si(110) Interface. <i>Applied Physics Express</i> , <b>2008</b> , 1, 061104	2.4	20
212	Time-resolved cathodoluminescence of Mg-doped GaIn. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 151901	3.4	19
211	Effect of native oxide mechanical deformation on InP nanoindentation. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 113509	2.5	7
210	Photoluminescence of near-lattice-matched GaIn/AlIn quantum wells grown on free-standing GaIn and on sapphire substrates. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 031907	3.4	7
209	Role of the buffer layer thickness on the formation of basal plane stacking faults in a-plane GaIn epitaxy on r-sapphire. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 011901	3.4	23
208	Structural and optical properties of nonpolar GaIn thin films. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 171904	3.4	56
207	SEM characterization of silicon nanostructures: can we meet the challenge?. <i>Scanning</i> , <b>2008</b> , 30, 310-6	1.6	3
206	Synthesis and luminescence properties of ZnO nanostructures produced by the sol-gel method. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 599-603	1.6	55



205	Growth of free-standing highly luminescent undoped and Mg-doped GaN thick films with a columnar structure. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 3131-3134	1.6	7
204	Surface morphology control of green LEDs with p-InGaN layers grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5166-5169	1.6	6
203	Dislocation generation at the coalescence of aluminum nitride lateral epitaxy on shallow-grooved sapphire substrates. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 221909	3.4	25
202	Correlation of spectral luminescence with threading dislocations in green-light-emitting InGaN quantum wells. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 231901	3.4	15
201	Al <sub>x</sub> Ga <sub>1-x</sub> N (0 ≤ x ≤ 1) nanocrystalline powder by pyrolysis route. <i>Journal of Crystal Growth</i> , <b>2007</b> , 308, 198-2036		4
200	Growth of InAs nanostructures on InP using atomic-force nanolithography. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 89, 945-949	2.6	6
199	Determination of the electronic band structure for a graded modulation-doped AlGa <sub>1-x</sub> In <sub>x</sub> GaN superlattice. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 142121	3.4	9
198	Basal-plane slip in InGa <sub>1-x</sub> GaN heterostructures in the presence of threading dislocations. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 171922	3.4	11
197	Mapping the electrostatic potential across AlGa <sub>1-x</sub> In <sub>x</sub> GaN heterostructures using electron holography. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 032101	3.4	24
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